



S8550

Features:

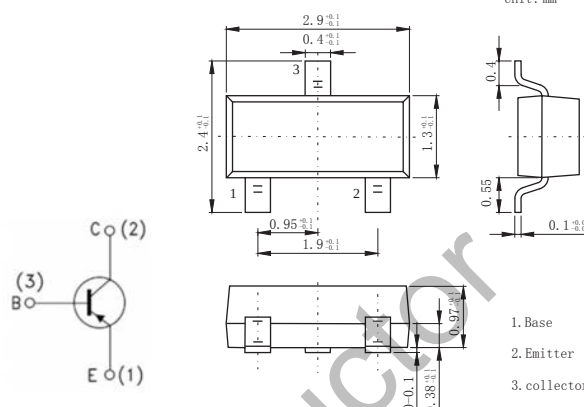
- ☐ Complimentary to S8050
- ☐ Collector current: $I_C = -0.5A$

Marking: 2TY

SOT-23



Unit: mm

Absolute Maximum Ratings* ($T_a = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
BV_{CBO}	Collector-Base Voltage	-40	V
BV_{CEO}	Collector-Emitter Voltage	-25	V
$BVEBO$	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.5	A
P_D	Collector Power Dissipation	0.6	W
T_j, T_{stg}	Junction and Storage Temperature	-55~+150	$^\circ C$

Electrical Characteristics* ($T_a = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	120	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

Classification Of h_{FE}

Classification	L	H	J
h_{FE1}	120-200	200-350	300-400

* Pulse Test: Pulse Width=20 μs , Duty Cycle $\leq 2\%$

Typical Characteristics

